

10/540261

JC17 Rec'd PCT/PTO 23 JUN 2005

00862.102568.

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:	)	
	:	Examiner: Not Yet Assigned
KAZUYA NOTSU, ET AL.	)	
	:	Group Art Unit: Not Yet Assigned
Application No.: U.S. National Stage of	)	
PCT/JP2004/018982,	:	
filed December 14, 1004	)	
	:	
Filed: Not Yet Assigned	)	
	:	
For: SEMICONDUCTOR MEMBER,	)	
MANUFACTURING METHOD	:	
THEREOF, AND SEMICONDUCTOR	)	
DEVICE	:	June 22, 2005

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed on the enclosed Form PTO-1449. Copies of the listed documents are also enclosed.

For a concise explanation of relevance of the non-English documents, the Examiner is referred to the enclosed English-language abstracts, and to pages 2 and 13 of the specification.

Some of the listed documents were cited in a PCT International Search report mailed February 8, 2005 for International Application No. PCT/JP2004/018982, which is the parent of the present application from which this application claims priority. A copy of this search report is also enclosed.

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Some of the listed documents were cited in a PCT International Search Report mailed March 29, 2005 for International Application No. PCT/JP2004/018981, which is the parent of the present application from which is application claims priority. A copy of this search report is also enclosed.

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our address given below.

Respectfully submitted,



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FORM PTO 1449 (modified)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)				ATTY DOCKET NO.  <b>00862.102568.</b>		APPLICATION NO. <b>10/1510261</b> <b>U.S. National Stage of</b> <b>PCT/JP2004/018982; filed</b> <b>December 14, 2004</b>	
				APPLICANT <b>KAZUYA NOTSU, ET AL.</b>			
				FILING DATE <b>Not Yet Assigned</b>		GROUP <b>Not Yet Assigned</b>	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		<b>5,221,413</b>	<b>06/22/93</b>	<b>Brasen et al.</b>	<b>117</b>	<b>89</b>	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
		<b>EP 1 248 294 A2</b>	<b>10/09/02</b>	<b>EPO</b>			
		<b>JP 2003-178977 A</b>	<b>06/27/03</b>	<b>Japan</b>			<b>Abstract</b>
		<b>JP 2003-282464 A</b>	<b>10/03/03</b>	<b>Japan</b>			<b>Abstract</b>
		<b>JP 2003-282463 A</b>	<b>10/03/03</b>	<b>Japan</b>			<b>Abstract</b>
		<b>JP 2004-342975 A</b>	<b>12/02/04</b>	<b>Japan</b>			<b>Abstract</b>
		<b>JP 2003-78118 A</b>	<b>03/14/03</b>	<b>Japan</b>			<b>Abstract</b>
		<b>JP 2003-78140</b>	<b>03/14/03</b>	<b>Japan</b>			<b>Abstract</b>
		<b>JP 11-195562</b>	<b>07/21/99</b>	<b>Japan</b>			<b>Abstract</b>
		<b>JP 7-302889</b>	<b>11/14/95</b>	<b>Japan</b>			<b>Abstract</b>
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
		<b>Michael I. Current, et al. "Atomic-layer Cleaving with SiGe Strain Layers for Fabrication on Si and Ge-rich SOI Device Layers", IEEE International SOI Conference, October 2001, pp. 11-12.</b>					
		<b>Shin-ichi Takagi, "Metal-Oxide-Semiconductor (MOS) device technologies using Si/Ge heretointerfaces", Oyo Buturi, Vol. 72, NO. 3, pp. 284-290, 2003.</b>					
		<b>T.A. Langdo, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 4256-4258 (2003).</b>					
		<b>D.J. Godbey, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 373-379 (1990).</b>					
		<b>D. Ferijoo, et al., J. Electro. Mat., vol. 23, no. 6, pp. 493-496 (1994).</b>					
		<b>A.H. Krist, et al., Appl. Phys. Lett., vol. 58, no. 17, pp. 1899-1901 (1991).</b>					
EXAMINER				DATE CONSIDERED			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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